

Notice of References CitedApplication/Control No.
09/901,109Applicant(s)/Patent Under Reexam
Droopad et al.Examiner
B. William BaumeisterArt Unit
2815

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^{*} A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.

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